

A 500MHz 1.5 MByte Cache with On-Chip CPU

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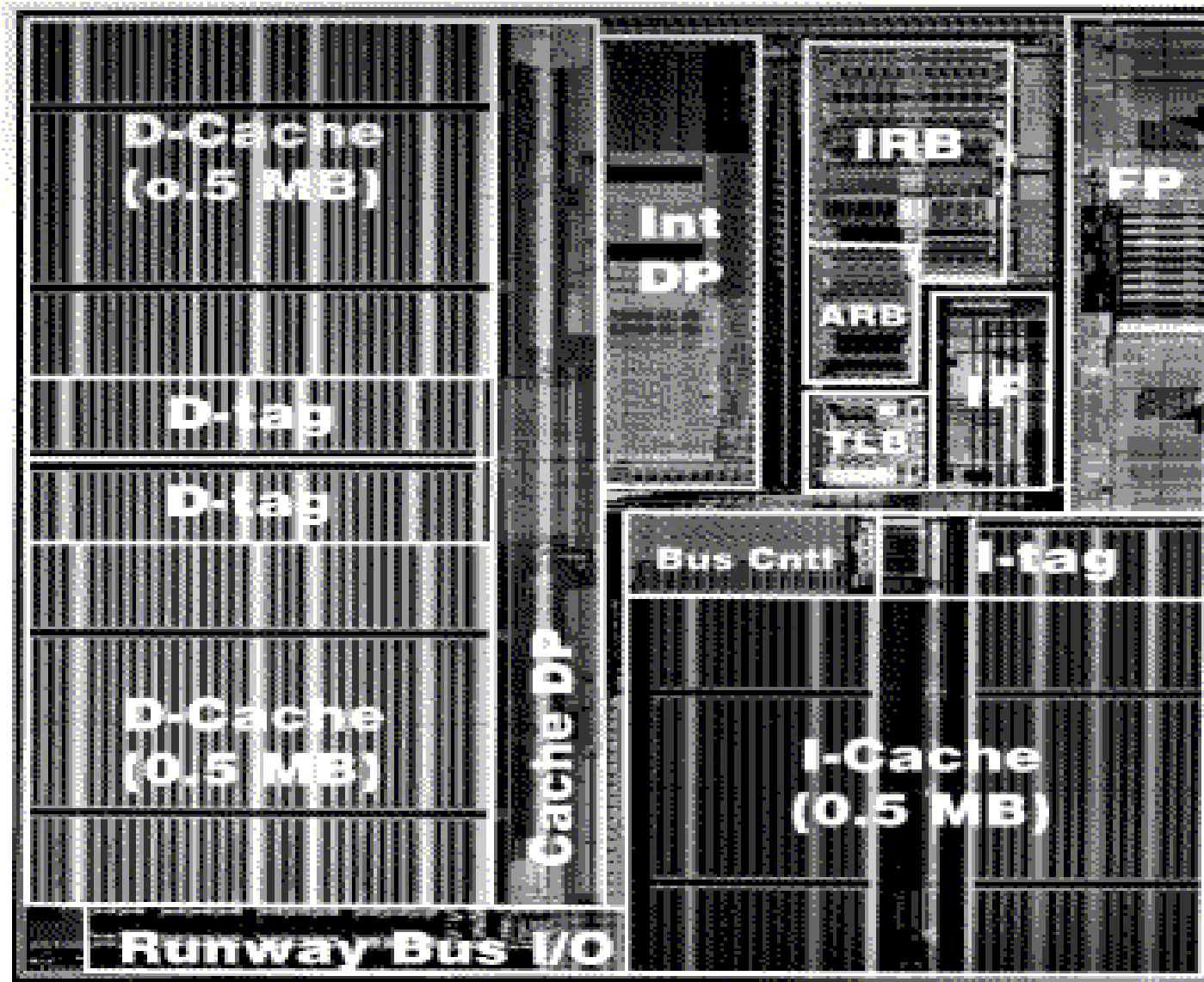
Outline

- Technology
- Cache Architecture
- Timing Control
- Address Paths
- Write Path
- Read Path
- Redundancy
- Performance
- Conclusions

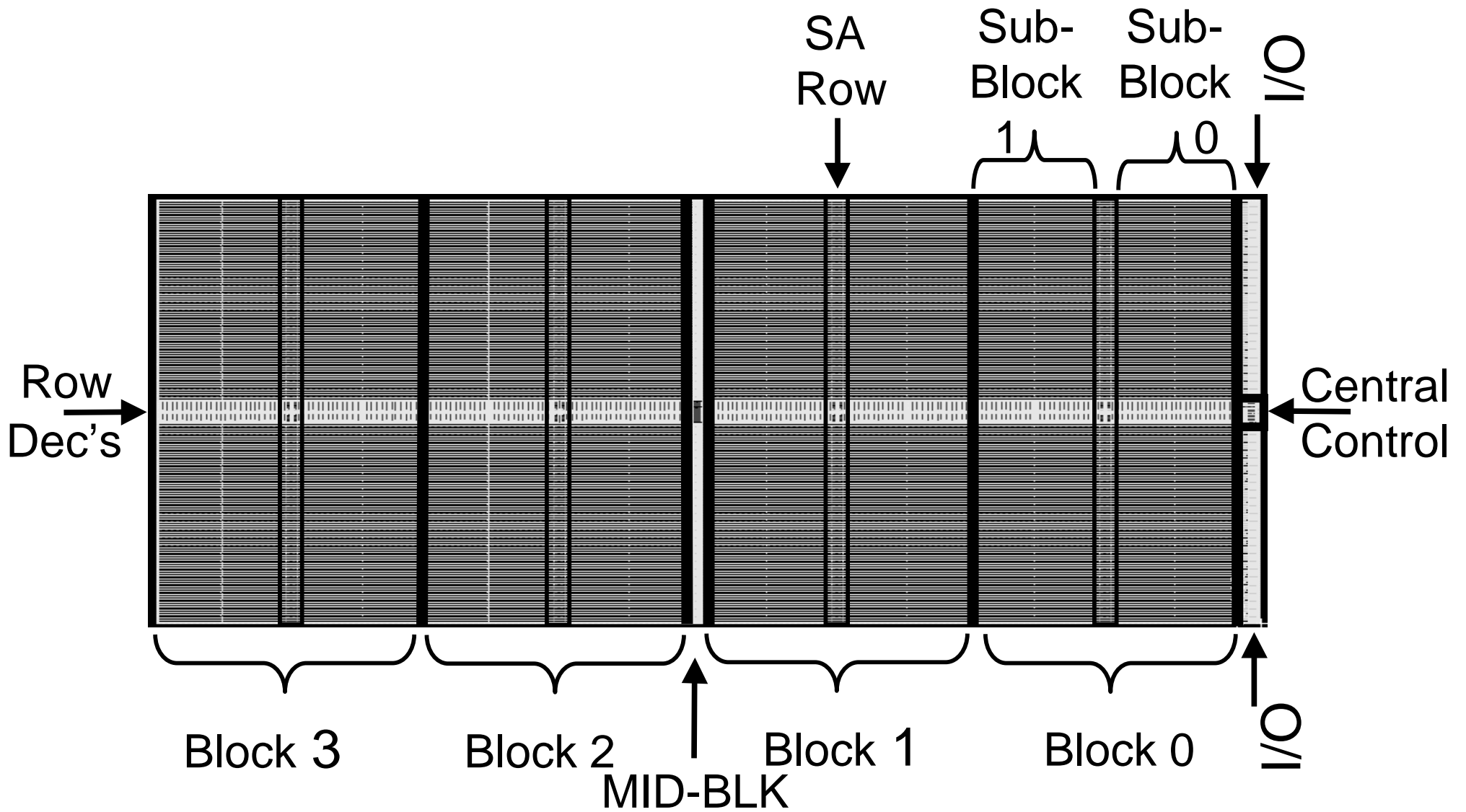
Technology

- 0.25um CMOS
- 5 levels of Al interconnect
- Sub-12 square micron memory cell
I_{cell} = 130uA at 110 Degrees C, 1.6v

Die Photo



1/4 MBYTE D-CACHE DATA STACK



BLOCK ARCHITECTURE

SUB-BLOCK 1

SUB-BLOCK 0

256 x 4, N	MCL	256 x 4, N
•	•	•
•	•	•
•	•	•
256 x 4, 1	MCL	256 x 4, 1
256 x 4, 0	MCL	256 x 4, 0
ROW DEC'S	MID CNTL	ROW DEC'S
256 x 4, 0	MCL	256x 4, 0
256 x 4, 1	MCL	256 x 4, 1
•	•	•
•	•	•
•	•	•
256 x 4, N	MCL	256 x 4, N

MCL

Left and Right:

BIT PRECHARGE

READ COL MUX

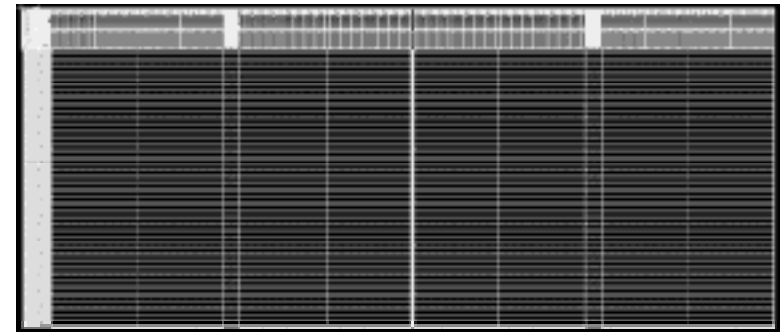
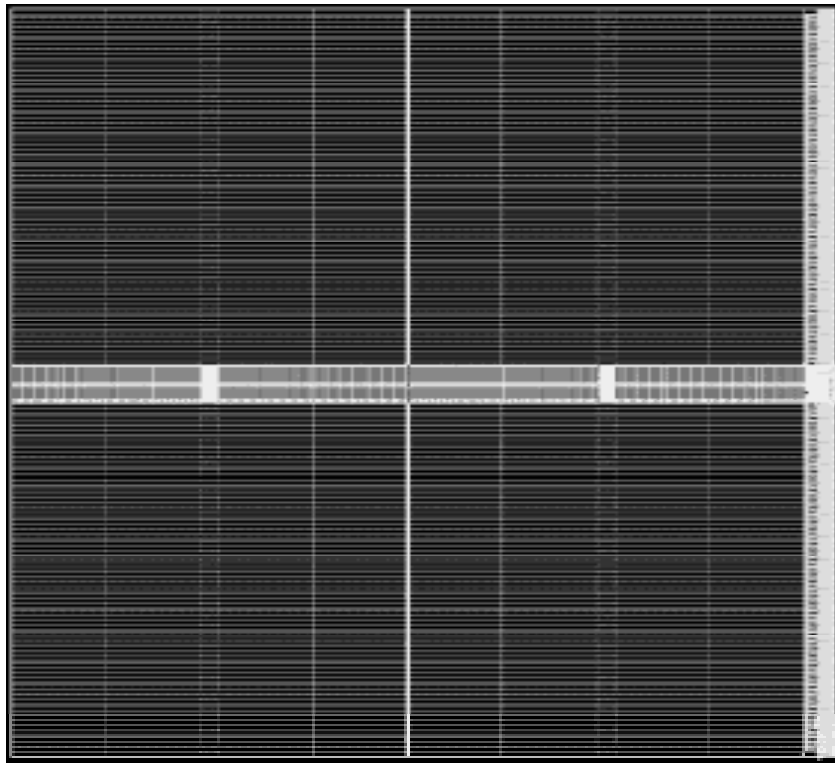
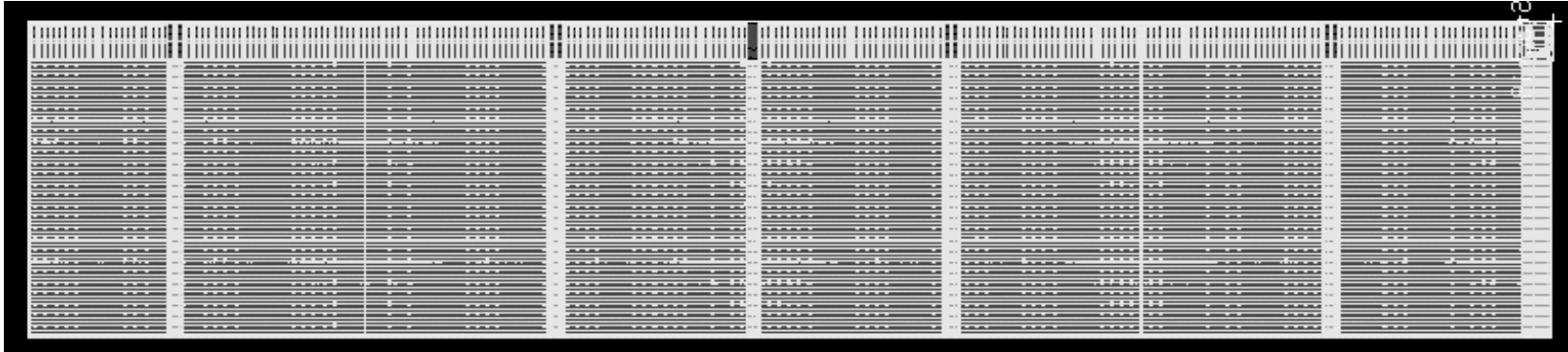
WRITE COL MUX

Shared:

SENSE-AMP

COL PRECHARGE

128KB D-CACHE TAG

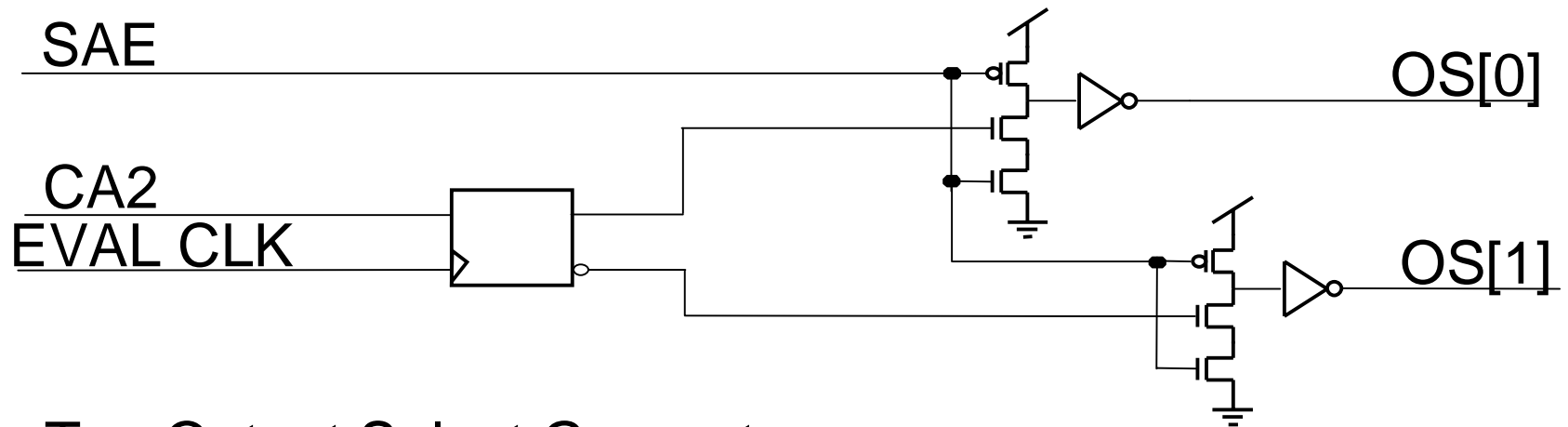


64KB I-CACHE TAG

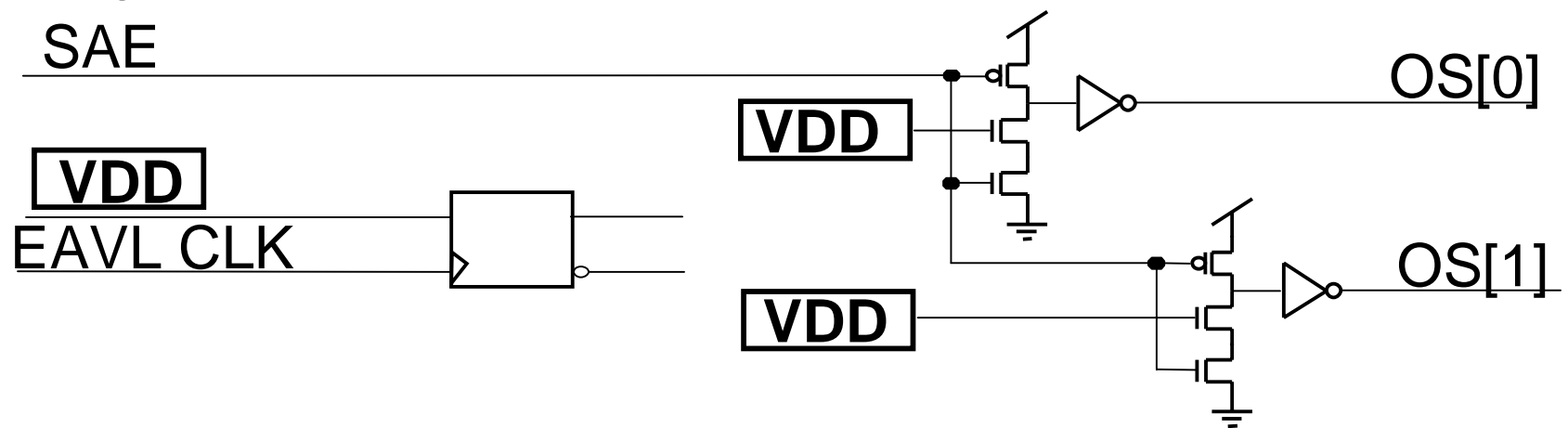
128KB I-CACHE DATA

BLOCK COMMONALITY TECHNIQUE

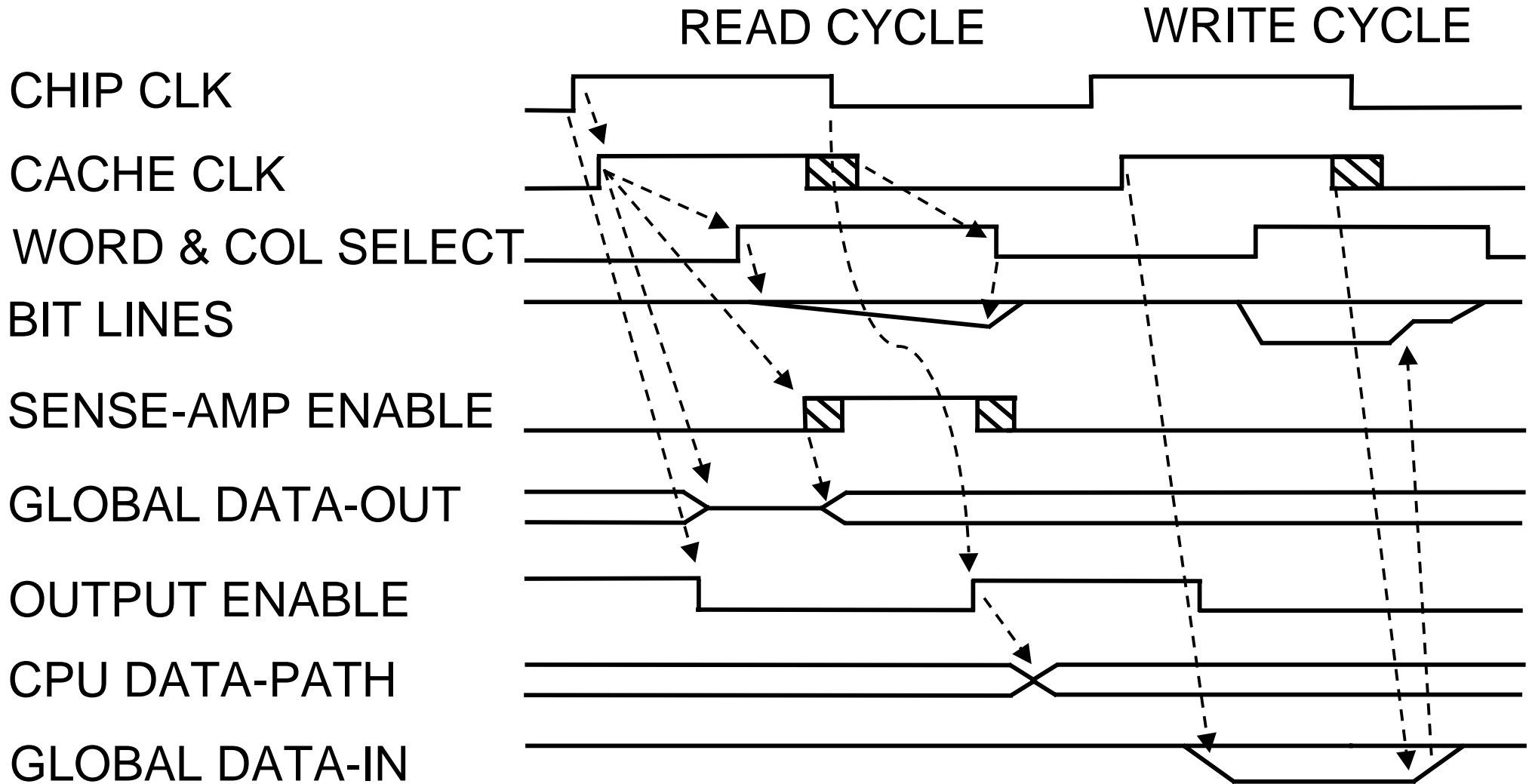
Data-Data Output Select Generators



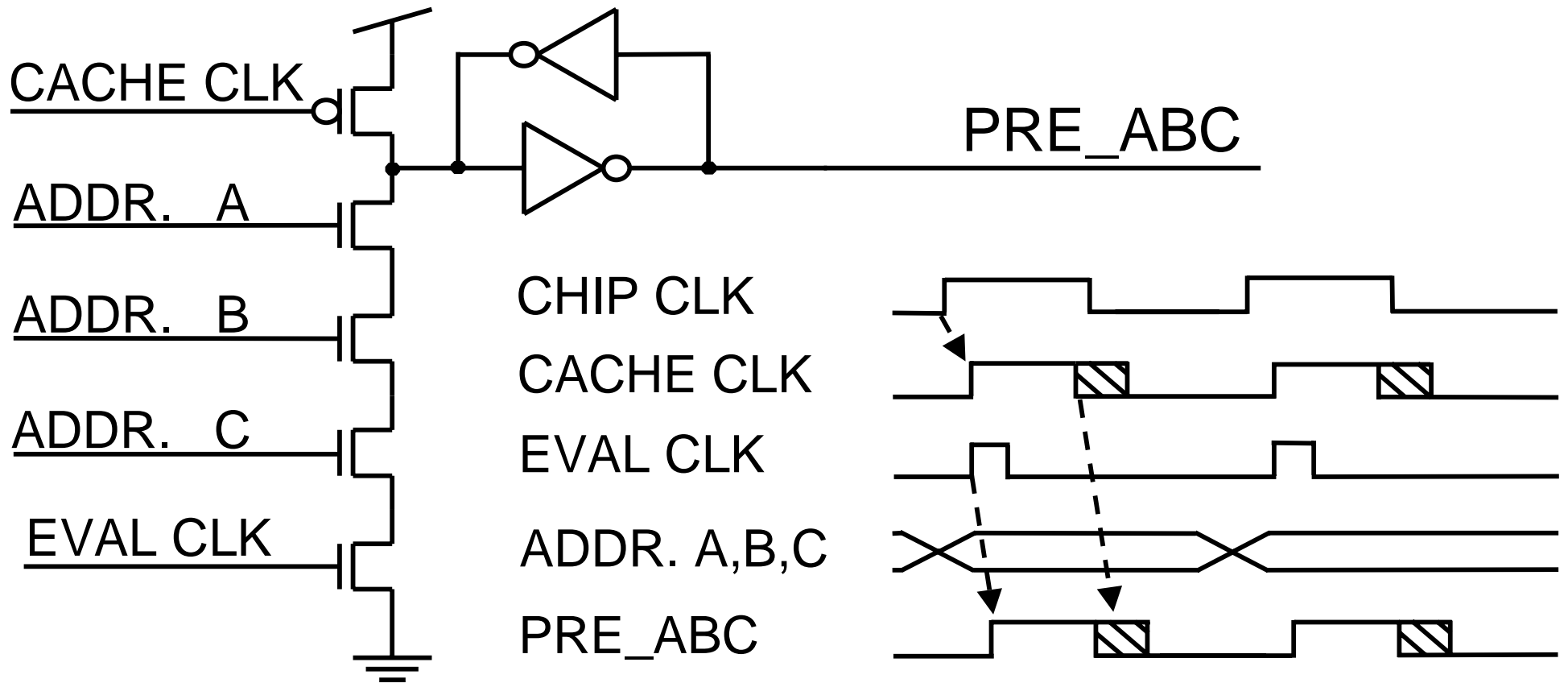
Data-Tag Output Select Generators



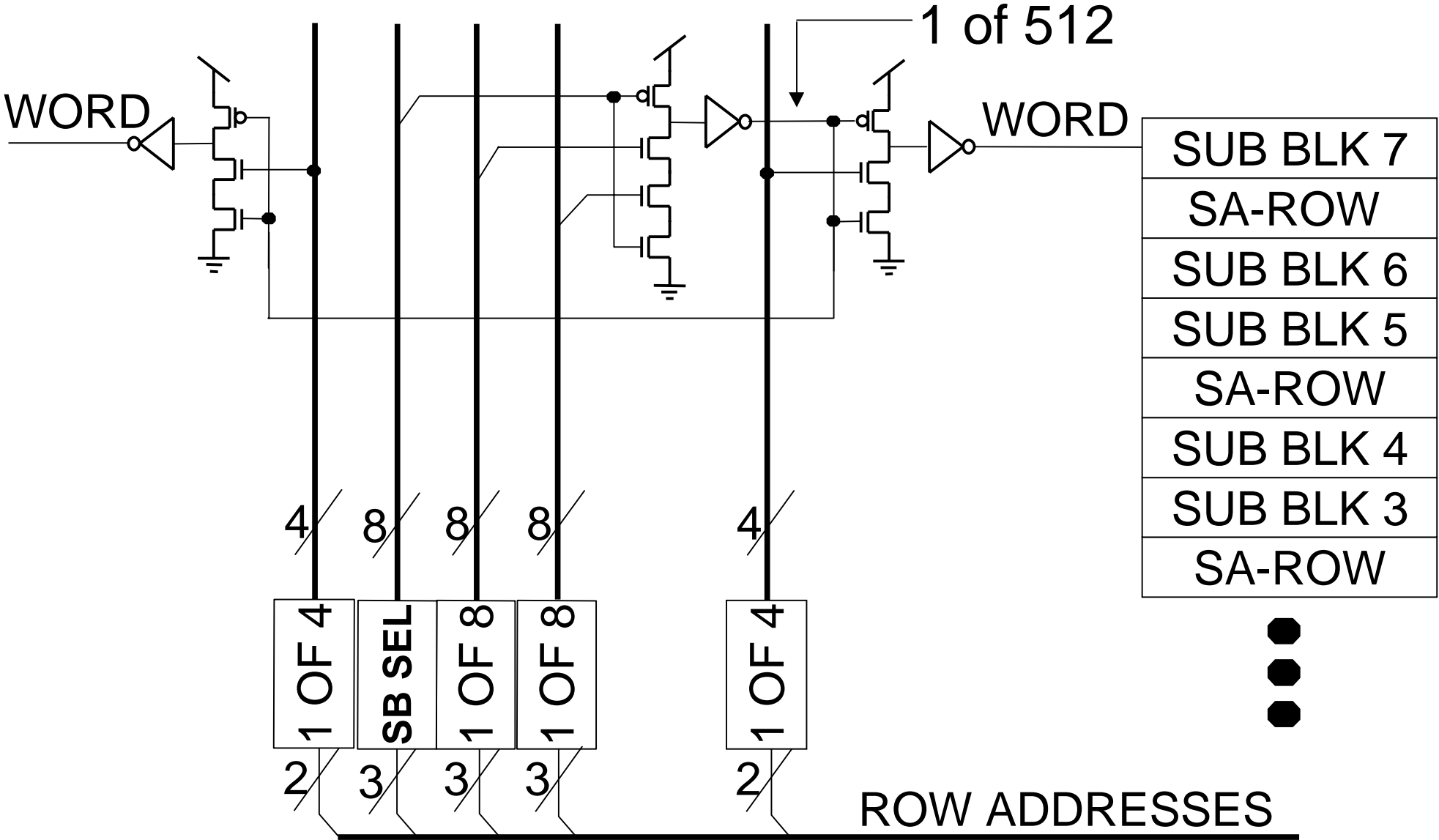
TIMING CONTROL



ADDRESS AND CONTROL PRE-DECODE

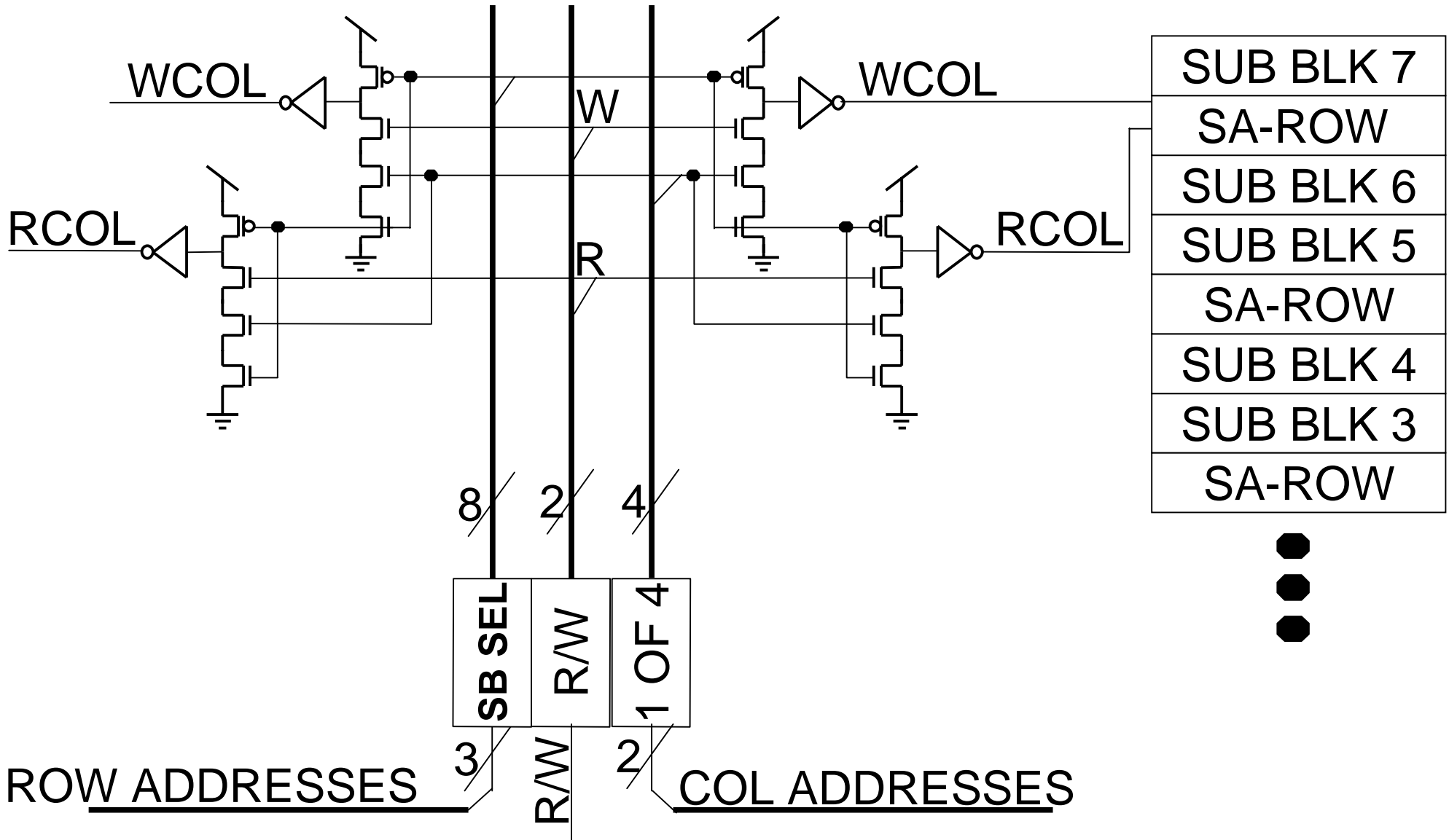


ROW ADDRESS DECODING

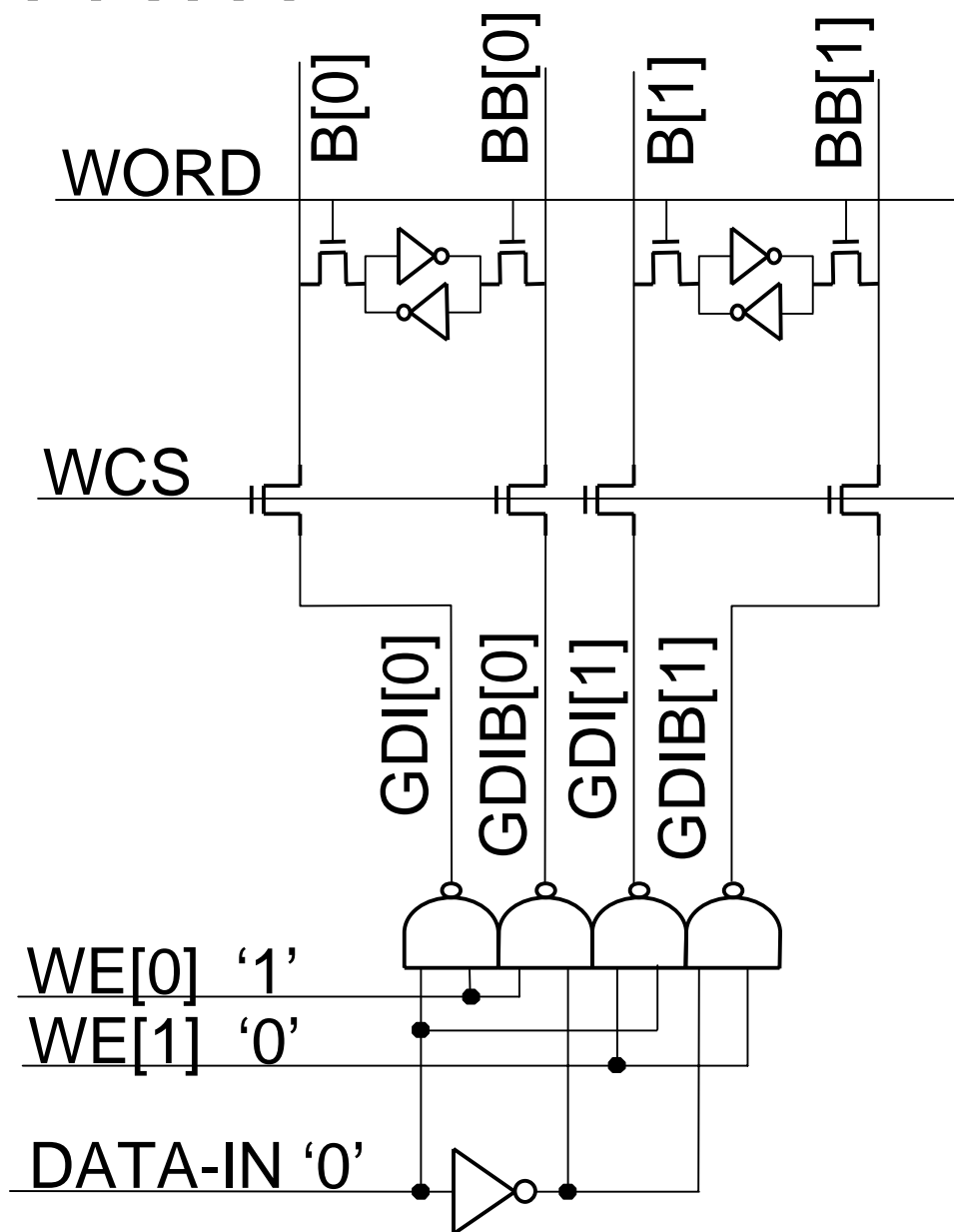
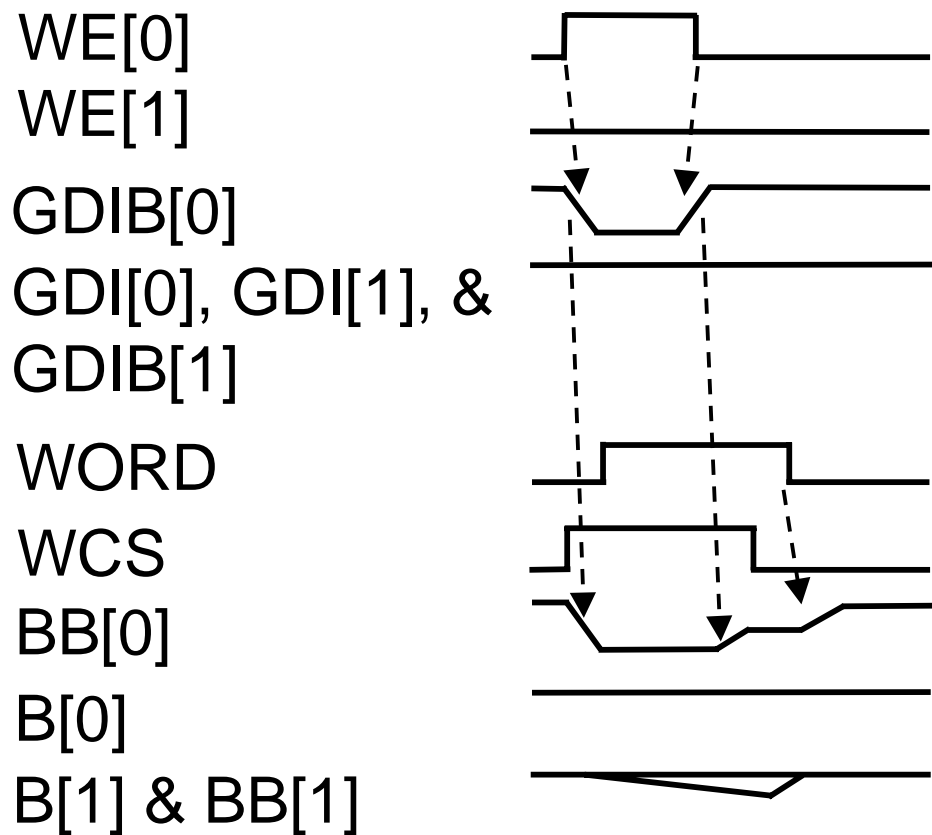


ROW ADDRESSES

COLUMN DECODING

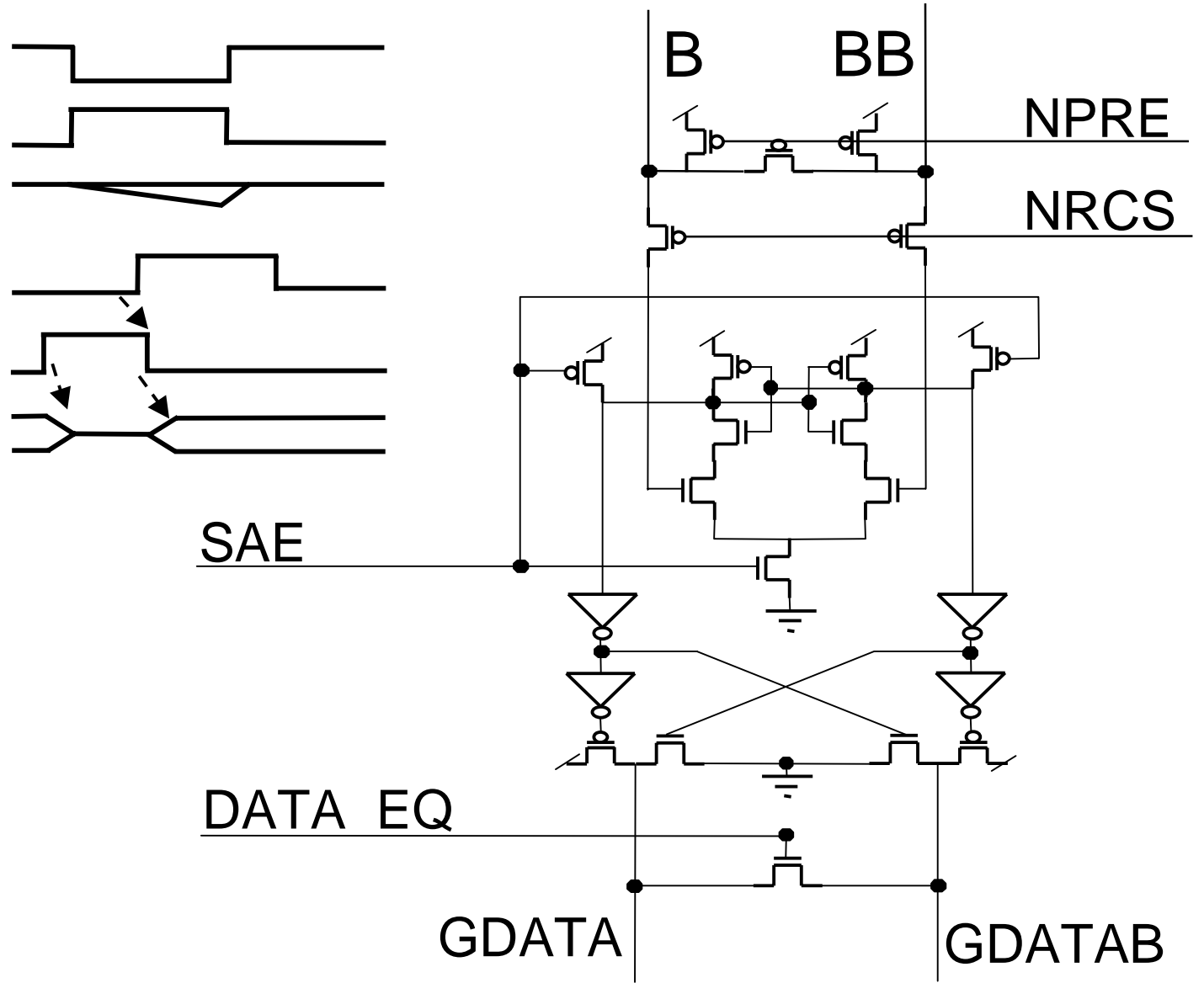


WRITE PATH

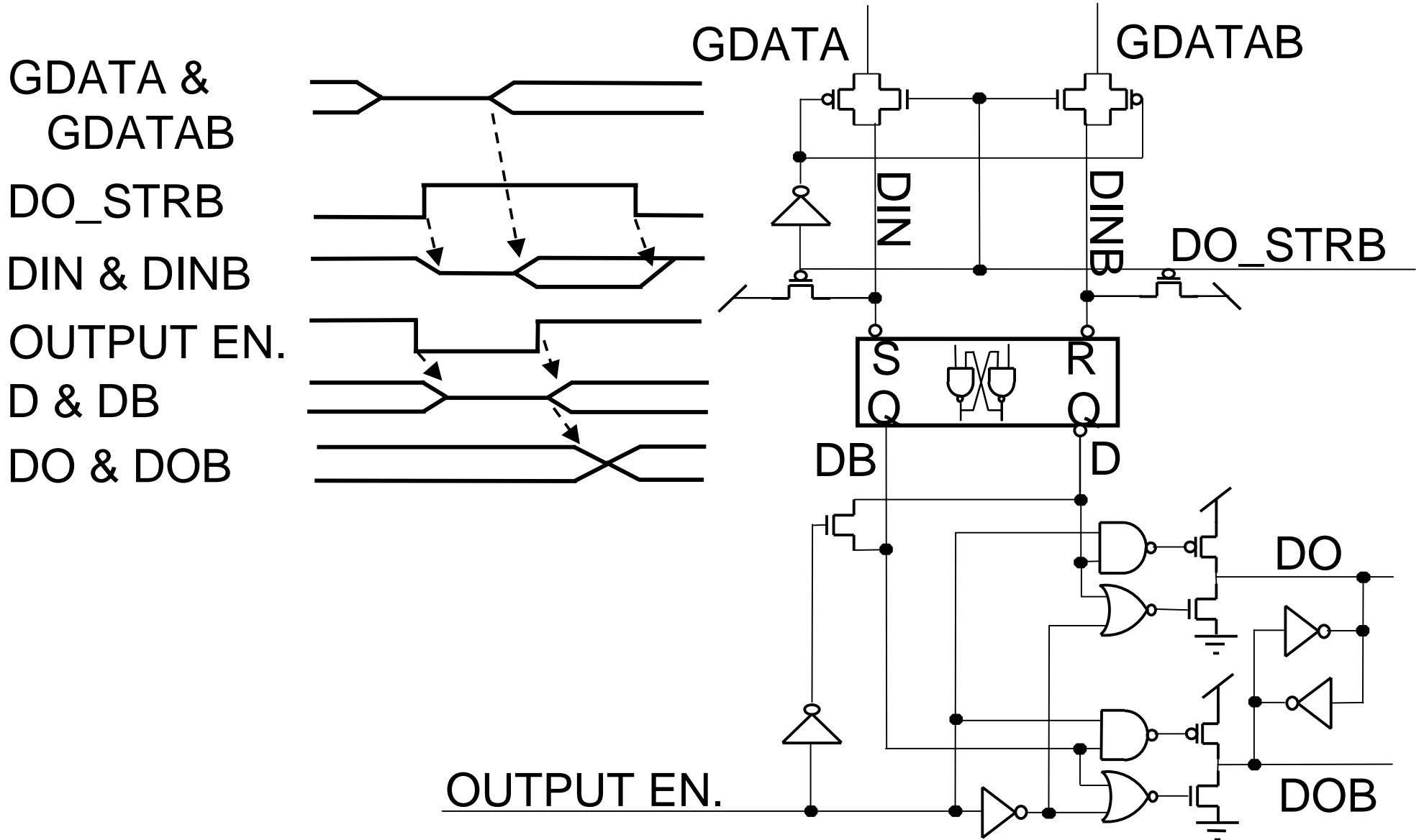


THE SENSE-AMP

NRCS
 WORD & NPRE
 B & BB
 SAE
 DATA EQ
 GDATA &
 GATAB

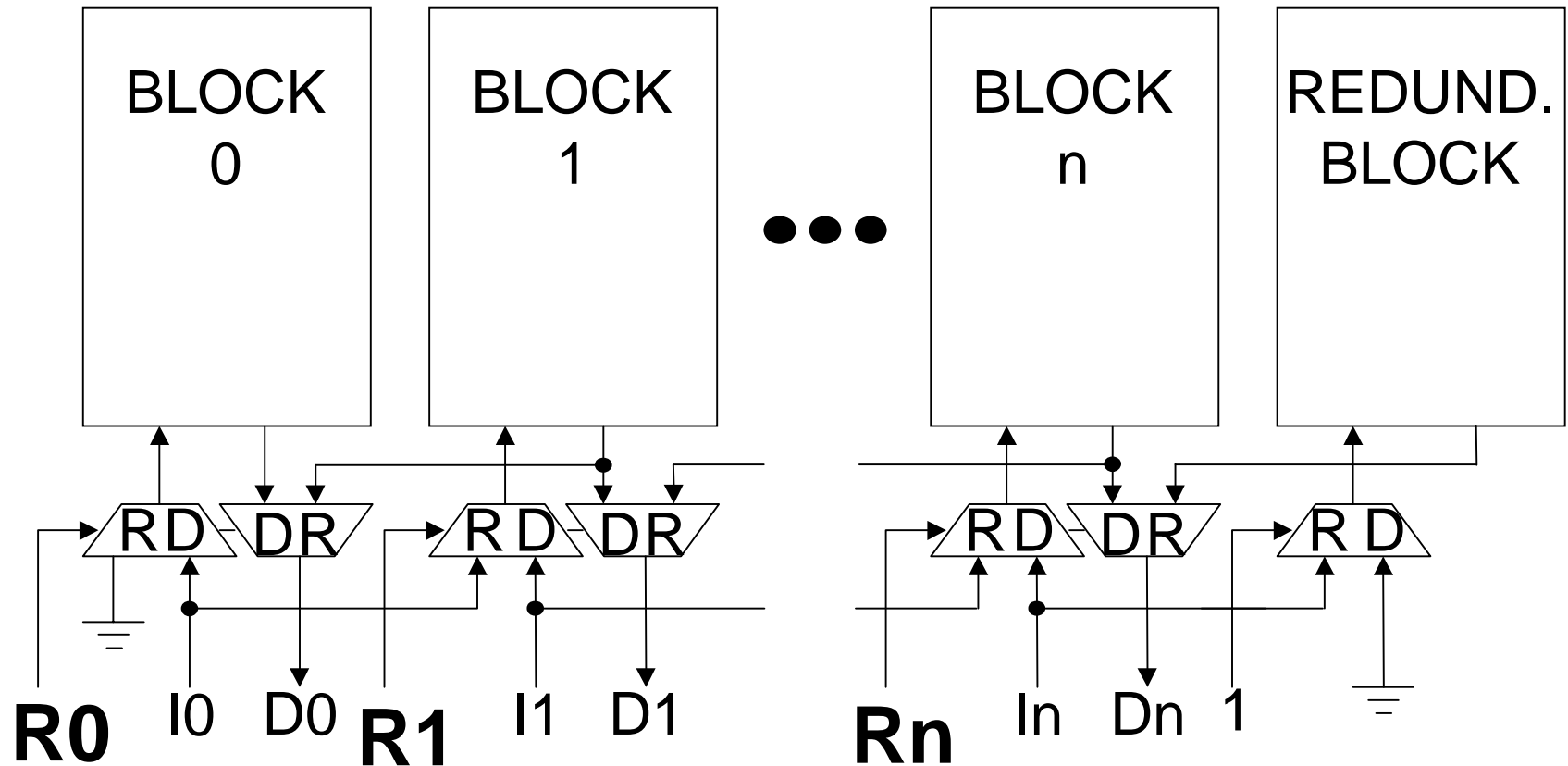


THE OUTPUT BUFFER

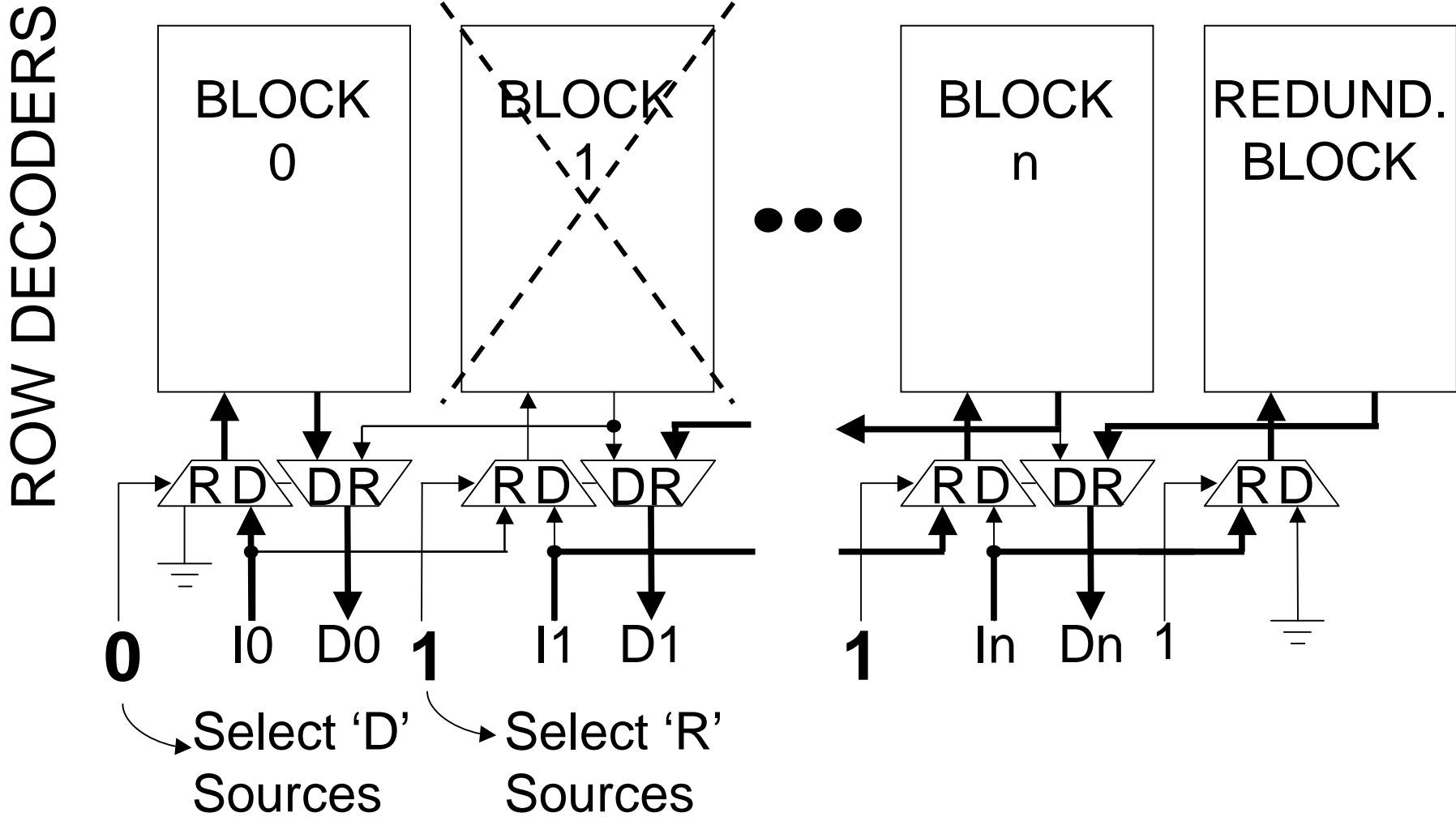


REDUNDANCY DATA STEERING

ROW DECODERS



REDUNDANCY DATA STEERING EXAMPLE



Conclusions

- Combining:
 - 0.25um technology
 - Data Driven Address Path
 - Low Skew Control Signal
 - Fully Differential Data Paths
- Yields:
 - 1.5 Mbytes
 - Greater than 500MHz Operation
 - Consuming < 12.5W @ 2.0V, 500MHz